2:1 MIPI D-PHY (4.5 Gbps) 4-Data-Lane & C-PHY (3.5 Gsps) 3-Data-Lane Switch

Description

The FSA646A can be configured as a four-data-lane MIPI, D-PHY switch or a three-data-lane MIPI, C-PHY switch. This single-pole, double-throw (SPDT) switch is optimized for switching between two high-speed or low-power MIPI sources. The FSA646A is designed for the MIPI specification and allows connection to a CSI or DSI module.

Features

- Switch Type: SPDT (10x)
- Signal Types:
 - ◆ MIPI, D-PHY V2.1 & C-PHY V1.2
- V_{CC}: 1.5 to 5.0 V
- Input Signals: 0 to 1.3 V
- R_{ON}:
 - 6 Ω Typical HS MIPI
 - 6 Ω Typical LP MIPI
- ΔR_{ON} : 0.1 Ω Typical LP & HS MIPI
- ΔR_{ON FLAT}: 0.9 Ω Typical LP & HS MIPI
- I_{CCZ}: 1 μA Maximum
- I_{CC}: 30 μA Maximum
- O_{IRR}: -24 dB Typical
- Bandwidth: 4.7 GHz Typical
- Xtalk: -30 dB Typical
- C_{ON}: 1.4 pF Typical
- Skew (P), Skew (O): 6 ps Typical

Applications

- Cellular Phones, Smart Phones
- Tablets
- Laptops
- Displays



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(Bottom View)

WLCSP36, 2.43x2.43x0.599 CASE 567XH

MARKING DIAGRAM

GQKK XYZ

GQ = Specific Device Code

KK = Assembly Lot

X = Year

Y = Work Week

Z = Assembly Location

ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

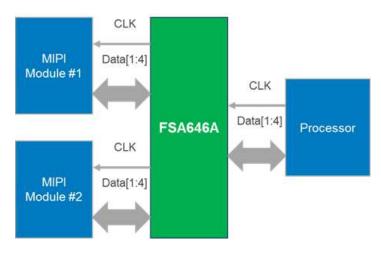


Figure 1. Typical D-PHY Application

PIN DESCRIPTIONS

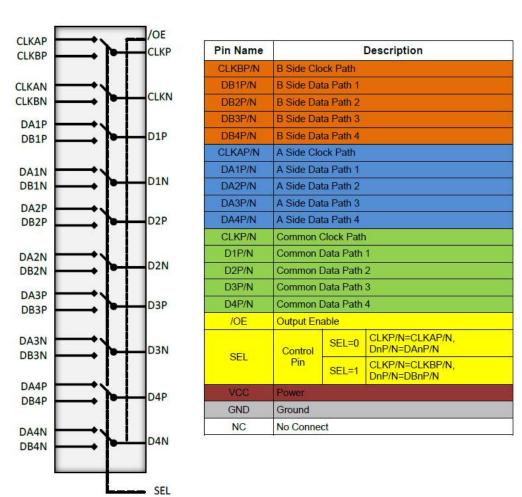


Figure 2. Analog Symbol

PIN DEFINITIONS

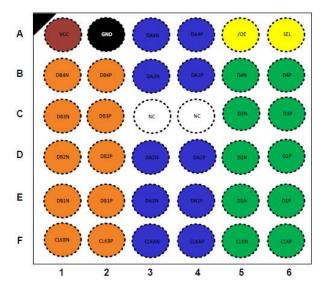


Figure 3. Top Through View

Table 1. BALL-TO-PIN MAPPINGS

Ball	Pin Name	Ball	Pin Name	Ball	Pin Name
A1	V _{CC}	C1	DB3N	E1	DB1N
A2	GND	C2	DB3P	E2	DB1P
А3	DA4N	C3	NC	E3	DA1N
A4	DA4P	C4	NC	E4	DA1P
A5	/OE	C5	D3N	E5	D1N
A6	SEL	C6	D3P	E6	D1P
B1	DB4N	D1	DB2N	F1	CLKBN
B2	DB4P	D2	DB2P	F2	CLKBP
B3	DA3N	D3	DA2N	F3	CLKAN
B4	DA3P	D4	DA2P	F4	CLKAP
B5	D4N	D5	D2N	F5	CLKN
B6	D4P	D6	D2P	F6	CLKP

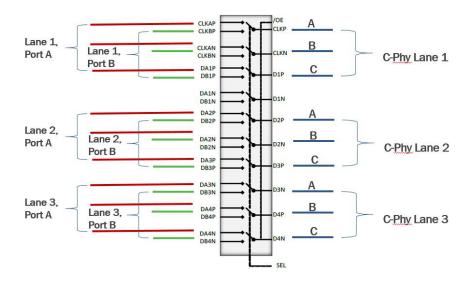


Figure 4. Recommended Configuration for C-PHY

TRUTH TABLE

SEL	/OE	Function
LOW	LOW	$CLK_P = CLKA_P$, $CLK_N = CLKA_N$, $Dn(P/N) = DAn(P/N)$
HIGH	LOW	$CLK_P = CLKB_P$, $CLK_N = CLKB_N$, $Dn(P/N) = DBn(P/N)$
X	HIGH	Clock and Data Ports High Impedance

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Parameter			Unit
V _{CC}	Supply Voltage		-0.5	6.0	V
V _{CNTRL}	DC Input Voltage (/OE, SEL) (Note 1)			V _{CC}	V
V_{SW}	DC Switch I/O Voltage (Note 1,2)			2.1	V
I _{IK}	DC Input Diode Current				mA
I _{OUT}	DC Output Current			25	mA
T _{STG}	Storage Temperature			+150	°C
ESD	Human Body Model, JEDEC: JESD22-A114	All Pins	2.0		kV
	Charged Device Model, JEDEC: JESD22-C101		0.5		

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

^{1.} The input and output negative ratings may be exceeded if the input and output diode current ratings are observed.

^{2.} V_{SW} refers to analog data switch paths.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min.	Max.	Unit	
V _{CC}	Supply Voltage		1.5	5.0	V
V _{CNTRL}	Control Input Voltage (SEL, /OE) (Note 3)		0	V _{CC}	V
V _{SW}	Switch I/O Voltage	HS Mode	0	0.425	V
	(CLKn, Dn, CLKAn, CLKBn, Dan, DBn)	LP Mode	-0.05	1.3	V
T _A	Operating Temperature		-40	+85	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

3. The control inputs must be held HIGH or LOW; they must not float.

DC AND TRANSIENT CHARACTERISTICS (T_A = 25°C unless otherwise specified)

				$T_A = -40 \text{ to } +85^{\circ}\text{C}$			
Symbol	Parameter	Conditions	V _{CC} (V)	Min.	Тур.	Max.	Unit
V _{IK}	Clamp Diode Voltage (/OE, SEL)	I _{IN} = -18 mA	1.5	-1.2		-0.6	V
V _{IH}	Input Voltage High	SEL, /OE	1.5 to 5	1.3			V
V _{IL}	Input Voltage Low	SEL, /OE	1.5 to 5			0.5	V
I _{IN}	Control Input Leakage (/OE, SEL)	V _{CNTRL} = 0 to V _{CC}	5	-0.5		0.5	μΑ
I _{NO(OFF)} I _{NC(OFF)}	Off Leakage Current of Port CLKAn, Dan, CLKBn and DBn	V _{SW} = 0.0 ≤ DATA ≤ 1.3 V	5	-0.5		0.5	μΑ
I _{A(ON)}	ON Leakage Current of Common Ports (CLKn, Dn)	V _{SW} = 0.0 ≤ DATA ≤ 1.3 V	5	-0.5		0.5	μΑ
l _{OFF}	Power-Off Leakage Current (All I/O Ports)	V _{SW} = 0.0 or 1.3 V	0	-0.5		0.5	μА
I _{OZ}	Off-State Leakage	V_{SW} = 0.0 \leq DATA \leq 1.3 V /OE = High	5	-0.5		0.5	μΑ
R _{ON_MIPI_HS}	ON_MIPI_HS Switch On Resistance for	S MIPI Applications SEL = V _{CC} or 0 V, CLKA,	1.5		6		Ω
	(Note 4)		2.5				
			3.3				
			5				
R _{ON_MIPI_LP}	Switch On Resistance for	I _{ON} = -8 mA, /OE = 0 V,	1.5		6		Ω
	LP MIPI Applications (Note 4)	SEL = V_{CC} or 0 V, CLKA, CLKB, DB _N or DA _N = 1.2 V	2.5				
			3.3				
			5				
$\Delta R_{ON_MIPI_HS}$	On Resistance Matching	I _{ON} = -8 mA, /OE = 0 V,	1.5		0.1		Ω
	Between HS MIPI Channels	SEL = V_{CC} or 0 V, CLKA, CLKB, DB _N or DA _N = 0.2 V	2.5				
	(Note 4)		3.3				
			5				
$\Delta R_{ON_MIPI_LP}$	On Resistance Matching	I _{ON} = -8 mA, /OE = 0 V,	1.5		0.1		Ω
	Between LP MIPI Channels	SEL = V_{CC} or 0 V, CLKA, CLKB, DB_N or $DA_N = 1.2$ V	2.5				
	(Note 4)		3.3				
			5				

$\textbf{DC AND TRANSIENT CHARACTERISTICS} \ (T_A = 25^{\circ}C \ unless \ otherwise \ specified) \ (continued)$

				T _A =	= -40 to +8	35°C	
Symbol	Parameter	Conditions	V _{CC} (V)	Min.	Тур.	Max.	Unit
R _{ON_FLAT_MIPI_HS}	On Resistance Flatness	I _{ON} = -8 mA, /OE = 0 V,	1.5		0.9		Ω
	for HS MIPI Signals (Note 4)	SEL = V_{CC} or 0 V, CLKA, CLKB, DB _N or DA _N = 0 to	2.5				
		0.3 V	3.3				
			5				
R _{ON_FLAT_MIPI_LP}	On Resistance Flatness	I _{ON} = -8 mA, /OE = 0 V,	1.5		0.9		Ω
	for LP MIPI Signals (Note 4)	(Note 4) $CLKB, DB_N \text{ or } DA_N = 0 \text{ to}$	2.5				
		1.3 V	3.3				
			5				
Icc	Quiescent Supply Current (Includes Change Pump)	$V_{SEL} = 0$ or V_{CC} , $I_{OUT} = 0$, /OE = 0 V	5			30	μΑ
I _{CCZ}	Quiescent Supply Current (High Impedance)	V _{SEL} = 0 or V _{CC} , I _{OUT} = 0, /OE = 0 V	5			1	μА
Гсст	Increase in I _{CC} Current Per Control Voltage and V _{CC}	$V_{SEL} = 0$ or V_{CC} , $/OE = 1.5 V$	5		1		μΑ

^{4.} Measured by the voltage drop at the indicated current through the switch.

AC ELECTRICAL CHARACTERISTICS (V $_{CC}$ = 3.3 V and T $_{A}$ = 25 $^{\circ}C$ unless otherwise specified)

				T _A =	= -40 to +8	85°C	
Symbol	Parameter	Conditions	V _{CC} (V)	Min.	Тур.	Max.	Unit
t _{INIT}	Initialization Time V _{CC} to Output (Note 5)	$R_L = 50 \Omega, C_L = 0 pF,$ $V_{SW} = 0.6 V$	1.5 to 5		60		μs
t _{EN}	Enable Time /OE to Output	$\begin{aligned} R_L &= 50 \ \Omega, \ C_L = 0 \ pF, \\ V_{SW} &= 0.6 \ V \end{aligned}$	1.5 to 5		60	150	μS
t _{DIS}	Disable Time /OE to Output	$R_L = 50 \Omega, C_L = 0 pF,$ $V_{SW} = 0.6 V$	1.5 to 5		35	250	ns
t _{ON}	Turn-On Time SEL to Output	$R_L = 50 \Omega, C_L = 0 pF, V_{SW} = 0.6 V$	1.5 to 5		350	1100	ns
t _{OFF}	Turn-Off Time SEL to Output	$R_L = 50 \Omega, C_L = 0 pF,$ $V_{SW} = 0.6 V$	1.5 to 5		125	800	ns
t _{BBM}	Break-Before-Make Time	$R_L = 50 \Omega, C_L = 0 pF,$ $V_{SW} = 0.6 V$	1.5 to 5	50		450	ns
t _{PD}	Propagation Delay (Note 5)	$C_L = 0 \text{ pF}, R_L = 50 \Omega$	1.5 to 5	30	67	100	ps
O _{IRR}	Off Isolation for MIPI (Note 5)	R_L = 50 Ω , f = 2250 MHz, /OE = HIGH, V_{SW} = 0.2 V_{PP}	1.5 to 5		-24		dB
X _{TALK}	Crosstalk for MIPI (Note 5)	R_L = 50 Ω , f = 2250 MHz, SEL = High, V_{SW} = 0.2 V_{PP}	1.5 to 5		-30	-25	dB
		R_L = 50 Ω , f = 2250 MHz, SEL = Low, V_{SW} = 0.2 V_{PP}			-30	-25	
BW	-3 db Bandwidth (Note 5)	$\begin{aligned} R_L &= 50 \ \Omega, \ C_L = 0 \ pF, \\ V_{SW} &= 0.2 \ V_{PP} \end{aligned}$	1.5 to 5		4.7		GHz
IL	Insertion Loss at 750 MHz (Note 5)	$R_L = 50 \Omega, C_L = 0 pF,$ $V_{SW} = 0.2 V_{PP}$	1.5 to 5		-0.7		dB

^{5.} Guaranteed by characterization.

HIGH-SPEED-RELATED AC ELECTRICAL CHARACTERISTICS

				T _A =	-40 to +8	35°C	
Symbol	Parameter	Conditions	V _{CC} (V)	Min.	Тур.	Max.	Unit
t _{SK(P)}	HS Mode Skew of Oppo- site Transitions of the Same Output (Note 6)	$\begin{aligned} R_L &= 50 \ \Omega, \ C_L = 0 \ pF, \\ V_{SW} &= 0.3 \ V \end{aligned}$	1.5 to 5		6		ps
t _{SK(O)}	HS Mode Skew of Channel-to-Channel Single-Ended Skew (Note 6)	$R_L = 50 \Omega, C_L = 0 pF,$ $V_{SW} = 0.3 V$	1.5 to 5		6		ps

^{6.} Guaranteed by characterization.

CAPACITANCE

			T _A =	-40 to +8	5°C	
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
C _{IN}	Control Pin Input Capacitance (Note 7)	V _{CC} = 0 V, f = 1 MHz		2.1		pF
C _{ON}	On Capacitance (Note 7)	V_{CC} = 3.3 V, /OE = 0 V, f = 2250 MHz (in HS common value)		1.4		
C _{OFF}	On Capacitance (Note 7)	V _{CC} and /OE = 3.3 V, f = 2250 MHz (both sides in HS common value)		0.9		

^{7.} Guaranteed by characterization.

The table below pertains to the Packaging information on the following page.

ORDERING INFORMATION

Part Number	Top Mark ^{ing}	Temperature Range	Package
FSA646AUCX	GQ	−40 to +85°C	36-Ball WLCSP, Non-JEDEC 2.43 x 2.43 mm, 0.4 mm Pitch

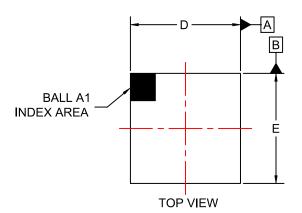




WLCSP36 2.43x2.43x0.599

CASE 567XH ISSUE O

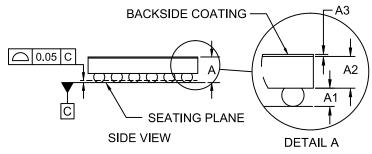
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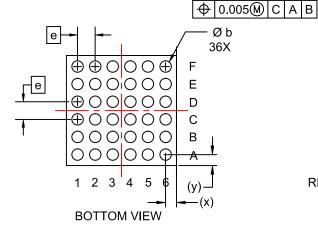


NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DATUM C APPLIES TO THE SPHERICAL CROWN OF THE SOLDER BALLS

	MILLIMETERS					
DIM	MIN.	NOM.	MAX.			
Α	0.558	0.599	0.640			
A1	0.174	0.194	0.214			
A2	0.362	0.380	0.398			
A3	0.022	0.025	0.028			
b	0.240	0.260	0.280			
D	2.400	2.430	2.460			
Е	2.400	2.430	2.460			
е	0.40 BSC					
х	0.200	0.215	0.230			
У	0.200	0.215	0.230			





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